



제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 26일(수), 09:00-10:30

Room H (하트 I, 6층)

E. Compound Semiconductors 분과 [WH1-E] Compound Semiconductor III

좌장: 김동현 박사(KANC)

<p>WH1-E-1 09:00-09:15</p>	<p>3-levels-stacked In_{0.53}Ga_{0.47}As MBCFETs with Regrown S/D Contacts In-Geun Lee¹, Hyeon-Bhin Jo¹, Sang-Tae Lee², Minwoo Kong⁴, Ji-Min Baek¹, Seung-Won Yun¹, Hyeon-Seok Jeong¹, Wan-Soo Park¹, Ji-Hoon Yoo¹, Su-Min Choi¹, Sang-Kuk Kim³, Jae-Gyu Kim³, Jacob Yun³, Ted Kim³, Tae-Woo Kim⁵, Dae-Hong Ko⁶, Jung-Hee Lee¹, Kwang-Seok Seo⁴, Chan-Soo Shin², and Dae-Hyun Kim¹ ¹Kyungpook National University, ²Korea Advanced Nano Fab Center, ³QSI Inc., ⁴Seoul National University, ⁵University of Ulsan, ⁶Yonsei University</p>
<p>WH1-E-2 09:15-09:30</p>	<p>Trap Behavior of Metamorphic HEMTs with Pulsed IV and 1/f Noise Measurements Ki-Yong Shin¹, Ju-Won Shin¹, Walid Amir¹, Jae-Phil Shim², Sang-Tae Lee², Hyun-Chul Jang², Kyung-Ho Park², Chan-Soo Shin², and Tae-Woo Kim¹ ¹School of Electrical, Electronic and Computer Engineering, University of Ulsan, ²Korea Advanced Nano Fab Center</p>
<p>WH1-E-3 09:30-09:45</p>	<p>Microcavity-integrated Flexible Mid-infrared Photodetector with Hetero-epitaxial Growth Seungwan Woo^{1,2}, Tae Soo Kim³, Jae-Hoon Han², In-Hwan Lee¹, Eung-Beom Yeon^{1,2}, Daehwan Jung², and Won Jun Choi² ¹Department of Materials Science and Engineering, Korea University, ²Center for Opto-electronic Materials and Devices, KIST, ³School of Electrical and Electronic Engineering, Yonsei University</p>
<p>WH1-E-4 09:45-10:00</p>	<p>Metal Contact Optimization of Quantum Dot Laser for Epitaxial Lift-Off Sung-Han Jeon^{1,2}, Dae-Hwan Ahn¹, Jindong Song¹, Won Jun Choi¹, Woo-Young Choi², Daehwan Jung¹, and Jae-Hoon Han¹ ¹Center for Opto-Electronic Materials and Devices, KIST, ²Department of Electrical and Electronic Engineering, Yonsei University</p>
<p>WH1-E-5 10:00-10:15</p>	<p>Fabrication and Characterization of Normally-Off β-Ga₂O₃ Thin-Film Phototransistor with A Thickness of 8-nm Youngbin Yoon¹, Youngki Kim¹, Wan Sik Hwang², and Myunghun Shin¹ ¹School of Electronics and Information Engineering, Korea Aerospace University, ²Department of Materials Engineering, Korea Aerospace University</p>
<p>WH1-E-6 10:15-10:30</p>	<p>Trap Analysis of AlGaIn/GaN HEMT with Different Al Composition Walid Amir¹, Ju-Won Shin¹, Ki-Yong Shin¹, Surajit Chakraborty¹, Jae-Moo Kim², Chu-Young Cho², Kyung-Ho Park², Takuya Hoshi³, Takuya Tsutsumi³, Hiroki Sugiyama³, Hideaki Matsuzaki³, and Tae-Woo Kim¹ ¹Department of Electrical, Electronic and Computer Engineering, University of Ulsan, ²Korea Advanced Nano Fab Center, ³NTT Device Technology Laboratories, NTT Corporation</p>